Vishay Semiconductors

Standard Recovery Diodes, (Stud Version), 85 A

FEATURES

- High surge current capability
- Stud cathode and stud anode version
- Leaded version available
- Types up to 1600 V V_{RRM}
- Compliant to RoHS directive 2002/95/EC
- Designed and qualified for industrial level

TYPICAL APPLICATIONS

- Battery chargers
- Converters
- Power supplies
- Machine tool controls
- Welding

PRODUCT SUMMARY			
85 A			

MAJOR RATINGS AND CHARACTERISTICS					
PARAMETER	TEST CONDITIONS	85H	UNITS		
PANAMEIEN	TEST CONDITIONS	10 TO 120	140/160		
1		85		A	
I _{F(AV)}	T _C	140	110	°C	
I _{F(RMS)}		1:	А		
I _{FSM}	50 Hz	17	А		
	60 Hz	18	~		
l ² t	50 Hz	14	A ² s		
1-1	60 Hz	13	A-5		
V _{RRM}	Range	100 to 1200	1400/1600	V	
TJ		- 65 to 180	- 65 to 150	°C	

ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS							
TYPE NUMBER	VOLTAGE CODE	V _{RRM} , MAXIMUM REPETITIVE PEAK REVERSE VOLTAGE V	V _{RSM} , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	I_{RRM} MAXIMUM AT T _J = T _J MAXIMUM mA			
	10	100	200				
	20	200	300				
85HF(R)	40	400	500				
	60	600	700	9			
	80	800	900				
	100	1000	1100				
	120	1200	1300				
	140	1400	1500	4.5			
	160	1600	1700	4.0			

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FORWARD CONDUCTION									
DADAMETED	SYMBOL	TEST CONDITIONS			85HF(R)				
PARAMETER	STMBOL	TEST CONDITIONS		10 to 120	140/160	UNITS			
Maximum average forward current	I _{F(AV)}	180° conduc	tion, half sine wa	ave	8	5	А		
at case temperature	·r(AV)	100 0011000			140	110	°C		
Maximum RMS forward current	I _{F(RMS)}				1:	33	Α		
		t = 10 ms	No voltage		1700 1800				
Maximum peak, one-cycle forward,		t = 8.3 ms	reapplied				А		
non-repetitive surge current	IFSM	t = 10 ms	100 % V _{RRM}		1450				
		t = 8.3 ms	reapplied	Sinusoidal half wave,	1500				
	l ² t	t = 10 ms	No voltage	initial $T_J = T_J$ maximum	14 500		– A ² s		
121 ((t = 8.3 ms	reapplied		13 500				
Maximum I ² t for fusing		t = 10 ms	100 /0 VRRM		10 500				
		t = 8.3 ms			9400				
Maximum I ² \sqrt{t} for fusing	l²√t	t = 0.1 ms to 10 ms, no voltage reapplied			16 000		A²√s		
Value of threshold voltage (up to 1200 V)	N	T _J = T _J maximum 0.68					68	v	
Value of threshold voltage (for 1400 V, 1600 V)	V _{F(TO)}				69	v			
Value of forward slope resistance (up to 1200 V)	-	T _J = T _J maximum			$r_{\rm f}$ $T_{\rm J} = T_{\rm J}$ maximum $\frac{1.62}{1.75}$		1.62		- mΩ
Value of forward slope resistance (for 1400 V, 1600 V)	I I f						75	- 11152	
Maximum forward voltage drop	V _{FM}	$I_{pk} = 267 \text{ A}, T_J = 25 \text{ °C}, t_p = 400 \mu\text{s} \text{ rectangular wave}$			1.2	1.4	V		

PARAMETER	SYMBOL	TEST CONDITIONS	85H	85HF(R)		
PARAMETER	STMBOL	TEST CONDITIONS	10 to 120	10 to 120 140/160		
Maximum junction operating and storage temperature range	T _J , T _{Stg}		- 65 to 180	- 65 to 150	°C	
Maximum thermal resistance, junction to case	R _{thJC}	DC operation	0.	0.35		
Maximum thermal resistance, case to heatsink Rthcs		Mounting surface, smooth, flat and greased	0.	25 K/W		
Maximum shock ⁽¹⁾			1500			
Maximum constant vibration (1)		50 Hz	2	20		
Maximum constant acceleration ⁽¹⁾		Stud outwards	5000			
		Not lubricated thread, tighting on nut ⁽²⁾	3.4	(30)		
Maximum allowable mounting		Lubricated thread, tighting on nut ⁽²⁾	2.3	2.3 (20)		
torque (+ 0 %, - 10 %)		Not lubricated thread, tighting on hexagon ⁽³⁾	4.2	4.2 (37)		
		Lubricated thread, tighting on hexagon (3)	3.2	(28)		
Approximate weight		Unleaded device	1	7	g	
Approximate weight		Onieaueu device	0	0.6		
Case style		See dimensions - link at the end of datasheet	DO-203AB (DO-5)			

Notes

(1) Available only for 88HF

⁽²⁾ Recommended for pass-through holes

⁽³⁾ Recommended for holed threaded heatsinks

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CONDUCTION ANGLE	SINUSOIDAL CONDUCTION	RECTANGULAR CONDUCTION	TEST CONDITIONS	UNITS			
180°	0.10	0.08					
120°	0.11	0.11					
90°	0.13	0.13	$T_J = T_J$ maximum	K/W			
60°	0.17	0.17					
30°	0.26	0.26					

Note

• The table above shows the increment of thermal resistance R_{thJC} when devices operate at different conduction angles than DC

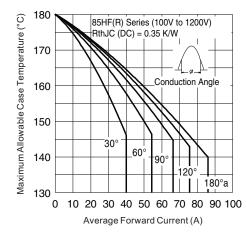


Fig. 1 - Current Ratings Characteristics

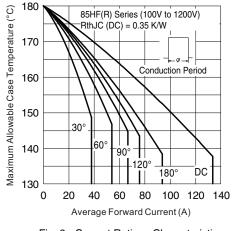
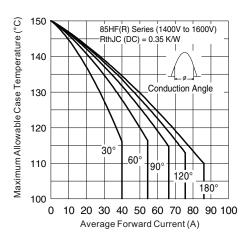
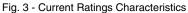


Fig. 2 - Current Ratings Characteristics





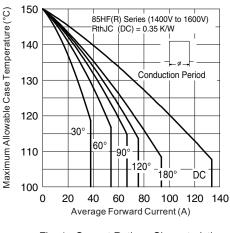
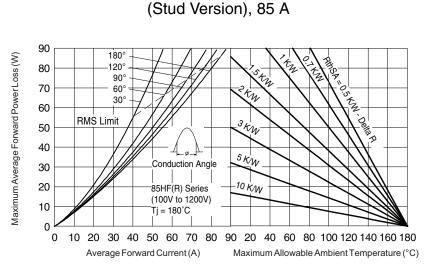


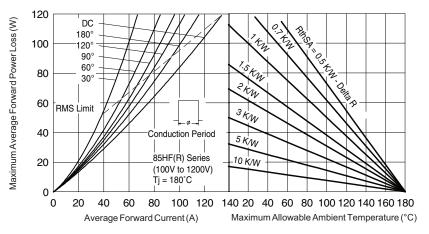
Fig. 4 - Current Ratings Characteristics

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Standard Recovery Diodes,







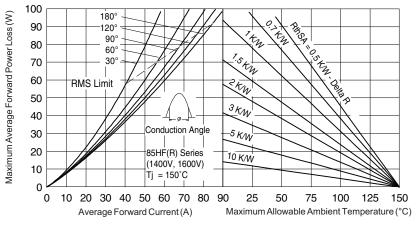
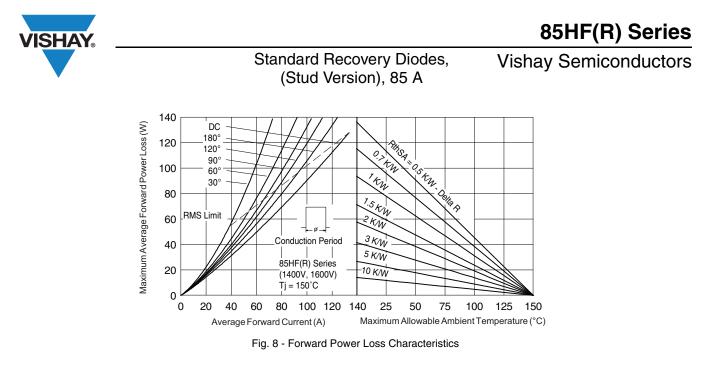


Fig. 7 - Forward Power Loss Characteristics



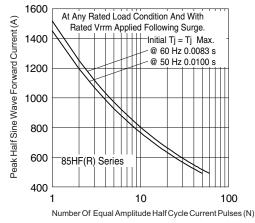


Fig. 9 - Maximum Non-Repetitive Surge Current

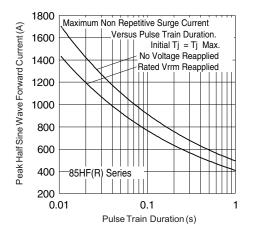


Fig. 10 - Maximum Non-Repetitive Surge Current

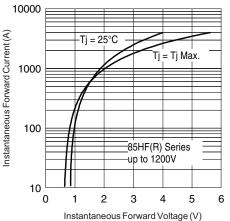
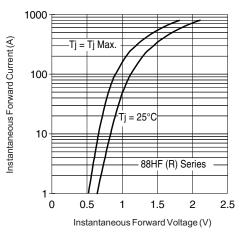
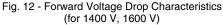


Fig. 11 - Forward Voltage Drop Characteristics (up to 1200 V)





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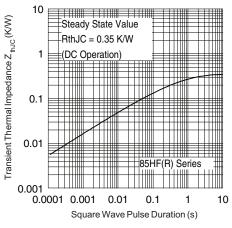


Fig. 13 - Thermal Impedance Z_{thJC} Characteristics

ORDERING INFORMATION TABLE

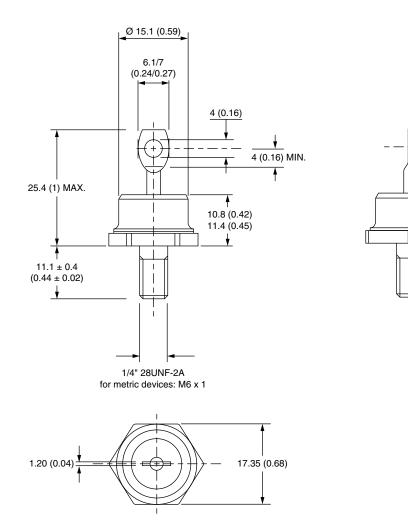
			_			
Device code	85	HF	R	160	М	
	(1)	(2)	(3)	(4)	(5)	
	1 -	85 =	- Standa	rd devic	e	
		86 =	Not iso	lated lea	ad	
		87 = Isolated lead with silicone sleeve				
		(red = Reverse polarity)				
		(blue = Normal polarity)				
		88 =	88 = Type for rotating application			
	2 -	HF	= Standa	ard diod	е	
	3 -	Non	None = Stud normal polarity (cathode to stud)			
		R = Stud reverse polarity (anode to stud)				
	4 -	Volt	age cod	e x 10 =	V _{RRM} (see Voltage Ratings table)
	5 -	Non	e = Stud	d base D	O-203A	AB (DO-5) 1/4" 28UNF-2A
		M =	Stud ba	ise DO-2	203AB (DO-5) M6 x 1 (not available for 88

LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?95342			

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DO-203AB (DO-5) for 85HF(R) and 86HF(R) Series

DIMENSIONS FOR 85HF(R) SERIES in millimeters (inches)



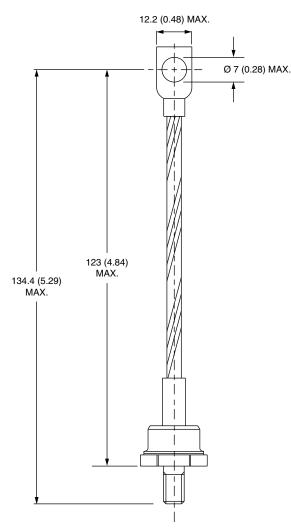


Vishay Semiconductors

DO-203AB (DO-5) for 85HF(R) and 86HF(R) Series



DIMENSIONS FOR 86HF(R) SERIES in millimeters (inches)





Vishay

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